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chambers have vacuum pressure generator for forming vacuum pressure therein.

8. (Amended) The multi-chamber system of an etching facility for manufacturing semiconductor devices according to claim 1, wherein the plurality of processing chambers have one common load lock chamber.

Three Times

20. (Twice Amended) A multi-chamber system of an etching facility for manufacturing semiconductor devices comprising:

a cassette stage for mounting a cassette having wafers stacked thereon;

a transfer path adjacent to the cassette stage for providing space for transportation of wafers, the transfer path being at atmospheric pressure and having a width slightly larger than a diameter of the wafers;

a plurality of processing chambers aligned in a plurality of layers parallel to and beside the transfer path; and

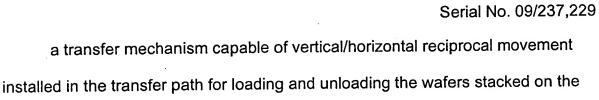
a transfer mechanism capable of vertical/horizontal reciprocal movement installed in the transfer path for loading and unloading the wafers stacked on the

cassette stage.

and IP a load lock chamber connected to one side of the processing chambers, the load lock chambers serving as a stand-by area for the waters

31. (Twice Amended) A multi-chamber system of an etching facility for manufacturing semiconductor devices comprising:

a first cassette stage for mounting a cassette having unprocessed wafers



cassette stage to the plurality of processing chambers.

- 22. (Amended) The multi-chamber system of an etching facility for manufacturing semiconductor devices according to claim 20, wherein the plurality of layers [multi-layers] of the processing chambers include [number] 2 to 5 layers.
- 24. (Amended) The multi-chamber system of an etching facility for manufacturing semiconductor devices according to claim 23, wherein the load lock chamber comprises:

a transfer arm for receiving wafers from the transfer mechanism and transferring the wafers to the processing [chamber] chambers;

an inner transfer device for moving the transfer arm; and gates formed on a side of the transfer path and [a side] sides of the processing chambers [chamber], respectively, the gates being selectively opened and closed to allow passage of the wafers.

26. (Amended) The multi-chamber system of an etching facility for manufacturing semiconductor devices according to claim 20, wherein the transfer mechanism comprises: